



CAS-Vacuum for Particle Accelerators

Fundamental of Vacuum Technology

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7th June 2017 Glumslov, Sweden



Contents

- Why do we need vacuum in particle accelerators?
- What is vacuum and vacuum ranges?
- Ideal gas law.
- Gas flow, conductance and pumping speed.
- Brief introduction to the gas sources in accelerators.
- Gas removal in accelerators: pumping mechanisms in UHV



Collisions between gas molecules and particles have to be minimized, otherwise:

Particle energy is reduced and trajectories are modified, so that:



Vacuum is also necessary:

- to avoid electrical discharge in high-voltage.
- To thermally isolate cryogenic devices.
- To avoid contamination of optics.



What is vacuum and vacuum ranges



- <u>Vacuum</u>:
 - <u>ISO 3529/1</u>: a dilute gas or the corresponding state at which <u>the</u> <u>pressure or density</u> is lower than that in the surrounding atmosphere.
 - <u>DIN 28400/1</u>: state where <u>the pressure</u> is smaller than 300 mbar, which is the lowest that may exist on the surface of earth!
- Partial emptiness of space, where some gases have been removed, so there is less gases (lower density) than the surrounding space of the same volume.



- A gas in a container exerts a force on the walls of that container.
- Pressure (p) is the ratio of the force (F) exerted perpendicularly to the surface of the wall (A)

 $\mathbf{p} = \frac{F}{A}$

... Pressure is a convenient parameter to characterize vacuum, however, below certain vacuum levels, other physical parameters, like <u>number</u> <u>density and mean free path</u> can characterize vacuum more precisely.





- The same units as for the pressure (p): force (F) over surface area (A).
 - SI units:

$$[p] = \frac{[F]}{[A]} = \frac{N}{m^2} = Pa$$

- One Pascal (Pa) is the pressure at which a force of 1N (1kg.m.s⁻¹) is exerted perpendicularly to a flat surface of 1 m².
- Pa or bar.
- 1mbar=100 Pa
- Commonly used:
 - 1 Torr= 133.3 Pa



Units

Units conversion

	Pa	bar	hPa	μ bar	torr	micron	atm	at	mm WC	psi	psf
Pa	1	1 · 10 ⁻⁵	1 · 10 ⁻²	10	7.5·10 ⁻³	7.5	9.87 · 10 ⁻⁶	1.02 · 10 - 5	0.102	1.45 · 10 ⁻⁴	2.09 \cdot 10^{-2}
bar	1 · 10 ⁵	1	1 · 10 ⁻³	1 · 10 ⁶	750	7.5·10 ⁵	0.987	1.02	$1.02 \cdot 10^{4}$	14.5	2.09·10 ³
hPa	100	1 · 10 ⁻³	1	1,000	0.75	750	9.87 · 10 ⁻⁴	1.02 · 10 - 3	10.2	1.45 · 10 - 2	2.09
μ bar	0.1	1.10-6	1 · 10 - 3	1	7.5 · 10 - 4	0.75	9.87 · 10 ⁻⁷	1.02 · 10 - 6	1.02 · 10 - 2	1.45 · 10 - 5	2.09.10-3
torr	1.33 · 10 ²	$1.33 \cdot 10^{-3}$	1.33	1,330	1	1,000	1.32 · 10 - 3	1.36 · 10 ⁻³	13.6	1.93 · 10 ⁻²	2.78
micron	0.133	1.33 · 10 ⁻⁶	$1.33 \cdot 10^{-3}$	1.33	1 · 10 ⁻³	1	1.32 · 10 - 6	1.36 · 10 - 6	1.36 · 10 - 2	1.93 · 10 - 5	2.78·10 ⁻³
atm	$1.01 \cdot 10^{5}$	1.013	1,013	$1.01\cdot 10^{6}$	760	7.6·10 ⁵	1	1.03	1.03 · 10 ⁴	14.7	$2.12 \cdot 10^{3}$
at	$9.81\cdot10^{4}$	0.981	981	$9.81\cdot 10^{5}$	735.6	$7.36 \cdot 10^{5}$	0.968	1	$1 \cdot 10^{-4}$	14.2	$2.04 \cdot 10^{3}$
mm WC	9.81	9.81 · 10 ⁻⁵	9.81 · 10 ⁻²	98.1	$7.36 \cdot 10^{-2}$	73.6	9.68.10-5	$1 \cdot 10^{-4}$	1	1.42 · 10 ⁻³	0.204
psi	6.89 · 10 ³	6.89·10 ⁻²	68.9	$6.89 \cdot 10^{4}$	51.71	$5.17\cdot10^{4}$	6.8·10 ⁻²	7.02 · 10 - 2	702	1	144
psf	47.8	4.78·10 ⁻⁴	0.478	478	0.359	359	4.72·10 ⁻⁴	4.87 · 10 ⁻⁴	4.87	6.94 · 10 ⁻³	1



Vacuum ranges are according to the American vacuum society (AVS) 1980.

Vacuum Range	Pressure Range (mbar)	Typical applications
Low	33 <p<1.0x10<sup>3</p<1.0x10<sup>	Vacuum cleaner, mechanical handling, vacuum forming,
Medium	1.0x10 ⁻³ <p<33< td=""><td>Vacuum drying, vacuum freeze (food industries)etc.</td></p<33<>	Vacuum drying, vacuum freeze (food industries)etc.
High (HV)	1.0x10 ⁻⁶ <p<1.0x10<sup>-3</p<1.0x10<sup>	Production of microwave, light bulbs, vapor deposition.
Very high (VHV)	1.0x10 ⁻⁹ <p<1.0x10<sup>-6</p<1.0x10<sup>	Electron microscopes, X-ray and gas discharge tubes, electron beam welding
Ultra-high (UHV)	1.0x10 ⁻¹² <p<1.0x10<sup>-9</p<1.0x10<sup>	Particle accelerators, space simulators, material research, semiconductors,
Extreme ultrahigh (XHV)	p≤1.0x10 ⁻¹²	Particle accelerators, space simulators, advanced semiconductor devices

Vacuum ranges in particle accelerators





OLAV-V

Kersevan

Status of LHC injectors and experimental areas Jose A. Ferreira Somoza



Basics of vacuum physics



Idea gas law

Assumptions for the ideal gas law

- The volume under discussion has a large number of molecules (e.g. at 1x10⁻⁹ mbar we have 2.5x10¹³ molecules).
- The distance between molecules is very large compared to their diameters (e.g. at 1x10⁻⁹ mbar the distance is 3x10⁻⁵m (dia. of molecules ~ 2-6x10⁻¹⁰m).
- Molecules are always in motion, in all directions.
- Molecules do not exert forces on each others (unless they collide).



- Gases have various properties: pressure (p), Temperature (T), mass (m), particle number (N), and volume (V).
 - Avogadro's constant: $N_A = 6.022142 \times 10^{23} mole^{-1}$
 - Mass density [kg.m⁻³]: $\rho = \frac{m}{v}$
 - Number density $[m^{-3}]: n = \frac{N}{V}$
 - Amount of substance : $v = \frac{N}{N_A}$

- Molar mass [kg.mol⁻¹]:
$$M = \frac{m}{v}$$



- For an ideal gas, if gas in state 1 then it can change into state 2 as follow:
- Boyle-Mariotte's law (p vs. V):

 $p_1.V_1 = p_2.V_2 = constant$ (for fixed: T, N)

• Charles' law (V vs. T):

 $\frac{V_1}{T_1} = \frac{V_2}{T_2} = constant \qquad(for fixed: p, N)$

• Gay Lussac's law (p vs. T):

 $\frac{p_1}{T_1} = \frac{p_2}{T_2} = constant \qquad \dots \dots (for fixed: V, N)$

• Avogadro's Law (V vs. N):

$$\frac{V_1}{N_1} = \frac{V_2}{N_2} = constant$$
(for fixed: T, p)



• Boyle's law (p vs. V):

p_1 . $V_1 = p_2$. $V_2 = constant$ (for fixed: T, N)



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• Charles's law (V vs. T):



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• Gay Lussac's law (p vs. T):



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• Avogadro's Law (V vs. N):

$$\frac{V_1}{N_1} = \frac{V_2}{N_2} = constant \dots (for fixed: T, p)$$



Two containers with the same volume at the same temperature and pressure should have the same number of particles.



Ideal gas law:

$$\frac{p.V}{T} = constant$$

- <u>The constant</u> is proportional to the <u>amount of gas</u>:
- When amount of gas is represented by mass (m):

$$p.V = m.Rs.T \qquad \qquad R_s = \frac{R}{M}$$

• When amount of gas is represented by particle number (N):

$$p.V = N.k.T$$

• When amount of gas is represented by number density (n):

$$p = n.k.T$$

 \circ When amount of gas is represented by amount of substance (v):

$$p.V = v.R.T$$

K=Boltzmann constant [J.K ⁻¹]	1.3806x10 ⁻²³
R = Gas constant [J.K ⁻¹ .mol ⁻¹]	8.314



• **Dalton's Law:** total pressure of a gas mixture is the sum of the

partial pressure of the individual components:

$$p = p_1 + p_2 + p_3 + \dots + p_i = \sum p_i$$





Velocity of gas molecule

- When gas molecules collide with each other or with the wall, their velocity value and direction change.
- Maxwell-Boltzmann velocity distribution:

$$\frac{dn}{dv} = \frac{2N}{\pi^{1/2}} \cdot \left(\frac{m}{2kT}\right)^{3/2} \cdot v^2 \cdot e^{-\left(\frac{mv^2}{2kT}\right)}$$

V: velocity of molecules (m/s)

n: number of molecules with v between v and v + dv

- N: the total number of molecules
- m: mass of molecules (kg)
- K: Boltzmann constant, 1.3806503×10⁻²³ m² kg s⁻² K⁻¹
- T: temperature (K)



Velocity of gas molecule





Velocity of gas molecule





Mean free path

The mean free path is the average distance that a particle can travel between two successive collisions with other particles or the walls.

$$\lambda = \frac{kT}{\sqrt{2}.\pi d^2.p}$$

- > λ :mean free path (m)
- ➤ d: diameter of molecule (m)
- ➤ T Temperature (K)
- P Pressure (Pascal)
- \succ k Boltzmann constant, 1.38 × 10⁻²³ m² kg s⁻² K⁻¹

For air at 20°C:

$$\lambda(cm) = \frac{0.007}{p(mbar)}$$



P (mbar)	1.0E+03	1.0E+00	1.0E-03	1.0E-06	1.0E-09
λ (cm)	0.000007	0.007	7	7000	7000000

• The impingement rate is number of molecules striking unit surface per unit time.

$$Z_A = \frac{2.635 \times 10^{22}.\,p}{\sqrt{TM}}$$

 Z_A - impingement rate (molc/cm⁻².s) p – pressure (mbar) T – temperature (K) M – molar mass (g/mol)

• <u>The time for monolayer formation</u>: is the time required for a freshly-formed surface to become covered with a monolayer of gas molecules

 $\tau = \frac{n_{mono}}{Z_A}$

au monolayer time formation (s) n_{mono} number of molecules per unit area (around 10¹⁹ molec/m²)

p	Pa	100	0.1	10-5	10-7	10 ⁻⁹ 10 ⁻¹¹	
	mbar	1	10-3	10-7	10-9		
tmono (air)		3.6 · 10 ⁻⁶ s	$3.6 \cdot 10^{-3}$ s	36 s	1 h	100 h	
tmono (H ₂ O)		2.8 · 10 ⁻⁶ s	$2.8 \cdot 10^{-3}$ s	28 s	47 min	78 h	
tmono (H ₂)		9.3 · 10 ⁻⁷ s	$9.3 \cdot 10^{-4}$ s	9.3 s	16 min	26 h	

$$\tau = \frac{3.2 \times 10^{-6}}{p}$$

for air at room temperture:



		Pressure					
		10 ⁵ Pa	10 ² Pa	10 ⁻¹ Pa	10 ⁻⁴ Pa	10 ⁻⁷ Pa	
		10 ³ mbar	10° mbar	10 ⁻³ mbar	10 ⁻⁶ mbar	10 ⁻⁹ mbar	
Particle Density,	$n (cm^{-3})$	10 ¹⁹	10 ¹⁶	10 ¹³	10 ¹⁰	107	
Mean Free Path,	λ (cm)	10-5	10-2	10	104	107	
						(= 100 km)	
Impingement Rate,	Z_{A} (s ⁻¹ cm ⁻²)	10 ²³	10^{20}	10 ¹⁷	1014	1011	
Collision Rate,	Z_{v} (s ⁻¹ cm ⁻³)	1029	10^{23}	10 ¹⁷	10 ¹¹	10 ⁵	
Monolayer Time,	τ	10 ns	10 µs	10 ms	10 s	3 h	



Gas flow, conductance and pumping speed



Gas flow

• Knudsen number characterizes the type of gas flow:



d: is the characteristics of the vessel (e.g. chamber diameter))

Three flow regime: vacuum Technology Know how by Pfeiffer Vacuum GmbH Viscous (continuous) : Kn <0.01</p> Gas molecules Intermediate (Knudsen): 0.01< Kn <0.5</p> collide with each other Molecular: kn>0.5 \succ 100 cm viscous Pipe diameter [cm] d Transitional Area 10 -Molecular 10-2 10² 10 10-5 10-4 10-3 10-1 10° 10¹ Pressure [mbar] Continuous flow Knudsen flow Molecular flow Gas molecules Kn < 0.01 0.01 < Kn < 0.5Kn > 0.5collide with Low vacuum Medium vacuum High/Ultra-high vacuum chamber walls



Gas flow

The flow rate of gas is defined as the transported gas per unit time, the amount of gas can be described as follow:

• Volume flow rate:
$$q_V = \frac{\Delta V}{\Delta t} = \dot{V}$$
 $[q_V] = m^{3.}s^{-1}$

• Mass flow rate:
$$q_m = \frac{\Delta m}{\Delta t} = \dot{m}$$
 $[q_m] = \text{kg.s}^{-1}$

• Molar flow rate:
$$q_{\nu} = \frac{\Delta \nu}{\Delta t} = \dot{\nu}$$
 $[q_{\nu}] = \text{mol.s}^{-1}$

• Particle flow rate:
$$q_N = \frac{\Delta N}{\Delta t} = \dot{N}$$
 $[q_N] = s^{-1}$



Throughput (Q)

- The flow rate as defined earlier could change along the tube, for example at the exit of the flow rate is higher than the beginning as the pressure drops along the tube end.
- Throughput or <u>pV flow</u>:

$$\mathbf{Q} = \boldsymbol{q}_{pV} = \boldsymbol{p} \cdot \dot{\boldsymbol{V}} \qquad [Q] = \text{mbar.l} \cdot s^{-1}$$





Pumping speed (S)

 Pumping speed (S): the gas volume flowing through the pump inlet per unit time.

$$S = V_{inlet} = q_{V,inlet}$$
 [S]=I/s

• The pumping speed relation with the throughput at the entrance of the pump is:

$$Q = p.S$$





- Impedance (Z): the gas flow through a pipe with resistance know as impedance (Z).
- The reciprocal of the impedance is the conductance C [l/s].

$$Q = \frac{(p_1 - p_2)}{Z} = \frac{\Delta p}{Z} = C.\Delta p$$

• C depends on the temperature, molecules, geometry and pressure (in the viscous regime).





Conductance in molecular flow

Total conductance

 In series: $Q_1 = C_1 (p_1 - p_2)$ Vacuum chamber $p_1 C_1 p_2$ C₂ P₃ Pump $Q_2 = C_{2} \cdot (p_2 - p_2)$ $Q_1 = Q_2 = Q = C_{total}(p_1 - p_3)$ $p_1 - p_2 = \frac{Q}{C_1}$ and $p_2 - p_3 = \frac{Q}{C_2}$ $p_1 - p_3 = \frac{Q}{C_{total}} = \frac{Q}{C_1} + p_2 + \frac{Q}{C_2} - p_2 = Q(\frac{1}{C_1} + \frac{1}{C_2})$ $\frac{1}{C_{total}} = \frac{1}{C_1} + \frac{1}{C_2} = \sum_{i=1}^{N} \frac{1}{C_i}$

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Conductance in molecular flow

Total conductance

- In parallel
- $Q_1 = C_1 \cdot (p_1 p_2)$ $Q_2 = C_2 \cdot (p_1 p_2)$
- $Q_{total} = Q_1 + Q_2 = C_{total} (p_1 p_2)$



•
$$Q_{total} = C_{total} (p_1 - p_2) = C_1 (p_1 - p_2) + C_2 (p_1 - p_2)$$

$$C_{total} = C_1 + C_2 = \sum_i^N C_i$$



Examples of conductance (molecular flow)



[C]=l/s [A]=cm²

• If the thickness is not negligible, the conductance is

 $C = 11.6 \times A \times \alpha$

Where α is the transmission factor



Examples of conductance (molecular flow)

Conductance of long circular tube:





Effective pumping speed

The pumping speed at any given point is not larger than the smallest conductance between that point and the pump



$$\frac{1}{S_{effective}} = \frac{1}{C} + \frac{1}{S_{nominl}}$$



Effective pumping speed

What is the effective pumping speed for the pump at the flange facing the beam path.

Input:

S_{nominal} for nitrogen=300l/s

CF150 elbow of ID=15.4 cm and length of 20x20 cm

Answer:

conductance of an orifice for nitrogen at room temp: $\mathbf{C} = 11.8 \times A \times \alpha$

 $A = \pi r^2 = \pi .7.7^2 = 186 cm^2$ (assuming entrance is also circular)

Determine the transmission probability for a circular elbow: $\frac{b}{r} = \frac{a}{r} = \frac{20}{7.7} = 2.6 \dots \alpha \sim 0.3$ $C = 11.8 \times A \times \alpha = 659 \text{I/s}$ $\frac{1}{S_{effective}} = \frac{1}{C} + \frac{1}{S_{nominl}} = \frac{1}{659} + \frac{1}{300}$ $S_{effective} = 206 \text{ l/S}$

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Figure 4.40 Axis length in a tube bend and a tube elbow.



Figure 4.41 Transmission probabilities of 90° tube elbows with circular cross sections and selected dimensions. As in the previous figures, the transmission probabilities apply to a mounting position between two chambers but not to a position between tubes.



Introduction to the gas sources in accelerators.



- Definitions:
 - Outgassing: spontaneous release of the gas from solid or liquid
 - Degassing: deliberate removal of the gas from solid or liquid
 - Desorption: release of adsorbed species from the surface of a solid or liquid.



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Gas sources





The ultimate pressure (p_u) is defined by the total outgassing (Q_{tot}) and the effective pumping speed (S_{eff}) .





Gas sources in accelerators

Thermal outgassing occurs when:

- Molecules <u>diffusing</u> through the bulk material of a vacuum chamber, entering the surface and desorbing from it.
- Molecules which have been adsorbed previously, usually during venting of the vacuum chamber, that <u>desorb</u> again, when the chamber is pumped to vacuum
- Thermal outgassing depends on: material, cleaning, history, treatments, pump down time,... etc





<u>Thermal outgassing:</u> example of outgassing rates after one hour in vacuum at room temperature:

Material	\mathbf{K}_{1} (mbar l s ⁻¹ cm ⁻²)
Aluminium (fresh)	9×10^{-9}
Aluminium (20 h at 100 °C)	5×10^{-14}
Stainless steel (304)	2×10^{-8}
Stainless steel (304, electropolished)	6×10^{-9}
Stainless steel (304, mechanically polished)	2×10^{-9}
Stainless steel (304, electropolished, 30 h at 250 °C)	4×10^{-12}
Perbunan	5×10^{-6}
Pyrex	1×10^{-8}
Teflon	8×10^{-8}
Viton A (fresh)	2×10^{-6}



Beam induced desorption (BID): outgassing stimulated by photons, ion or electrons created by high energy, high intensity beams.

Beam stimulated desorption is characterised by η - the desorption yield:

number of desorbed molecules

number of particle impinging the surface

- η depends on many parameters:
- incident particle: type and energy,
- material,
- surface roughness,
- cleanliness of the surface,
- history of the material.
- Temperature.
- Integrated dose
- Particle flux.



Photon-stimulated desorption (PSD)



Synchrotron radiation	\checkmark
Photoelectrons and scattered photons	
Gas molecules	• •

When photoelectrons arrive or leave the surface, they desorb the gases from the surface.



Photon-stimulated desorption (PSD)

<u>Conditioning</u> is the process of which reduction of the BID yield (η) with the accumulated dose (D_i) of the particles:

$$\eta = \eta_o D_i^{-\alpha}$$



Gas sources in accelerators

Photon-stimulated desorption (PSD)

 Experiments were performed to measure the PSD yield and its evolution with the beam dose for various material, incident angle, beam energy...



PSD yield vs. dose for Al after bakeout.





PSD yield vs. dose for st. steel after bakeout.



PSD yield vs. dose for OFHC copper after bakeout



<u>Type equation here.Photon-stimulated desorption (PSD)</u>

Total photon flux $\dot{\Gamma}$ [photons/s] around electron storage ring:

$$\dot{\Gamma} = = 8.08.10^{17}$$
. I. E

I – machine current [mA]

Outgassing (Q_{PSD}) due to PSD:

$$q_{PSD} = \eta \dot{\Gamma} \longrightarrow \frac{molecules}{s}$$

 $Q_{PSD} = K\eta \dot{\Gamma} \longrightarrow \frac{mbar l}{s}$

K – converts number of molecules to pressure units 4.04x10⁻²⁰ [mbar*l/molecule]

 η – desorption yield

Knowing the gas load (outgassing) due to PSD (Q_{PSD}) , thermal outgasing $(Q_{thermal})$ and the target pressure (*P*) the effective pumping speed S_{eff} can be calculated.

$$S_{eff} = \frac{Q_{PSD} + Q_{thermal}}{P}$$



Ion induced desorption:

In positively charged rings, the created ions from the residual gas are repelled from the positive beam to the walls.

Ions can gain energies which are effective in desorbing the molecules bounded to the chamber walls, as there is more gas more ionization occurs, resulting a continues increase in the pressure.

$$Q = \eta \sigma p \frac{I}{e} + Q_{thermal}$$

- η: the molecular desorption yield (molecules/ion).
- σ the ionization cross section of the residual gas molecules
- p: pressure
- I: average beam current
- e: the unit charge.
- *Q_{thermal}*: thermal outgassing





Gas removal in accelerators: pumping mechanisms in UHV



Gas removal in UHV



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Gas removal in UHV



Example: Turbomolecular Pump

Gas is transmitted as momentum is transferred to the gas molecules thereby achieving a directed movement.

The momentum transfer take place through a quickly turning blades of a turning rotor.

Example: Sputter Ion Pump, Getter pump, Cryo pump

Principle: gas molecules are fixed to a surface inside the wall of the pump.



Blade rotational speed 1000 – 1500 Hz

Pressure range: 10⁻¹ till 10⁻¹⁰ mbar, (with backing pump connected in series). Usual operational pressure < 10⁻⁵ mbar. **S (pumping speed)** does not depend significantly on the mass of the molecule.

(compression ratio)

$$\mathbf{K_o} = \frac{P_{outlet}}{P_{inlet}}$$

depends exponentially on the wall speed and square root of the gas molecule mass.



Turbomolecular Pump



Turbo molecular and roughing pump connected in series: from 1 bar (atmospheric pressure) until ~10⁻¹⁰ mbar

Turbomolecular pumping speeds: 10 l/s - 25,000 l/s.

Turbomolecular pumps are widely used in particle accelerators for:

- evacuating vacuum systems from atmospheric to ultra high vacuum,
- Testing (leak tests),
- Conditioning (bakeouts),
- High gas loads,
- For accelerator operation with beam capture pumps take over,



Capture pumps: getters

Capture pumps are vacuum pump in which the molecules are retained by sorption; chemical combination or condensation on internal surfaces within the pump. store gases that are pumped

- Sputter ion pumps.
- sublimating the reactive metal *in situ:* evaporable getters or sublimation pumps,
- dissolving the surface contamination into the bulk of the getter material by heating: non-evaporable getters (NEG); the dissolution process is called activation.

LABORATORY Capture pumps: sputter ion pumps (SIP)

Penning cell + HV

Ē





• The high magnetic field cause the electrons to go into spiral paths (preventing them from reaching to the anode).

Ψŀ

- While this the electrons strike the molecules and ionize them.
- Ions forced toward the cathode at high velocity.
- Ions strike the cathode and impact case sputtering of the cathode material.
- The cathode material will cover the internal walls of the pump.
- The ions are chemically and physically reacts with the cathode material.



Sputter ion pumps has three pumping mechanisms:

- Chemical adsorption onto the reactive metal layer (Ti) deposited on anode and subsequent burial by additional metallic atoms of gas molecules: all gases except rare gases,
- Implantation of gas ions in the cathode (not permanent), and of energetic neutrals bounced back from the cathode in the deposited film: only mechanism of pumping for rare (noble) gases,
- **Diffusion** into the cathode and the deposited film: only H₂



Diode configuration (cell cross-section)



Evaporable Getters

Evaporable getters: TSP – Titanium Sublimation Pump

Ti is the **sublimated** metal. Ti filaments are heated up to 1500°C reaching Ti vapor pressure which is deposited on the surrounding surfaces creating a chemically active surface where gas molecules are captured.

When the deposited film is saturated, new sublimation is needed to recover the initial pumping speed.

Sticking probablities: $H_2: 0.01 \le \alpha \le 0.1$ $CO: 0.5 \le \alpha \le 1$

Film capacity:

- For CO, one monolayer adsorbed,
- For of O₂ several monolayers,
- For N₂ fraction of monolayer

Hydrogen diffuses in the Ti film \rightarrow much higher capacity





- NEG pumps sorb gases by a chemical reaction. They use very reactive alloys, generally made of Ti, Zr, which are configured in a high efficiency getter cartridge structure.
- Pumping of the different gases:
 - Active gases, like O₂, N₂, H₂O, CO, CO₂ impinging on the cartridge surface are dissociated and permanently trapped, in the form of stable chemical compounds.
 - Hydrogen is very effectively pumped by the NEG. hydrogen atoms diffuse inside the getter bulk and dissolve as a solid solution.
 - Noble gases (and CH₄ at room temperature) are not pumped



Courtesy of Paolo Chiggiato JUAS

On activation the oxide layer at the surface of NEG is diffused to the bulk of the material creating clean, chemically active surface where gas molecules are captured.

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Non-Evaporable Getters (NEG)

NEG materials are produced industrially by powder technology. The powder is sintered to form discs or strips.

A typical alloy produced by SAES Getter is St707 made of Zr (70%), V (25%), Fe (5%).

The **high porosity of NEG materials** allows pumping of relatively high quantities of gas without reactivation. After 40 venting cycles (with nitrogen) and reactivation 80% pumping speed is conserved.





Distributed pumping





NEG coatings

NEG-coating transforms a vacuum chamber from a gas source to a vacuum pump.



The technology of coating vacuum chambers by magnetron sputtering was developed at CERN for the warm sections of LHC. Nowadays it is also widely applied in synchrotron radiation sources.



NEG film characteristics:

- Film composition: Ti (30%), Zr (40%), V (30%).
- Thickness ~1 um,
- Activation temperature 200°C for 24 h,
- Low PSD (Photon stimulated desorption),
- Sticking probability similar to TSP.

Disadvantage of NEG: has limited capacity and activation cycles.

NEG coatings



Photon stimulated desorption (PSD) measurements at ESRF (beamline D31).

Linear Photons Dose (ph/m)





- You may not need to deal with the vacuum fundamentals in your daily work, however, you still need to know how the different parameters in your system will affect your vacuum.
- Gas sources are important part which need to be under our control at all stages, in order to achieve the required pressure.
- Relating outgassing, pressure, conductance and pumping speed together, will allow you to design a vacuum system.
- I gave you the fundamentals but as you know, "the devil is in the details" and this is what my colleagues will give you in the coming days.



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Thank you for your attention & Wish you great time here!



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